

L Number	Hits	Search Text	DB	Time stamp
1	20770	print with head	USPAT; US-PGPUB	2003/10/28 11:59
2	486	(print with head) and (drive with transistor)	USPAT; US-PGPUB	2003/10/28 11:59
3	172	((print with head) and (drive with transistor)) and oxide	USPAT; US-PGPUB	2003/10/28 11:59
4	150	((print with head) and (drive with transistor)) and oxide) and @ad<20020108	USPAT; US-PGPUB	2003/10/28 11:53
5	39038	print with head	EPO; JPO; DERWENT; IBM_TDB	2003/10/28 11:59
6	125	(print with head) and (drive with transistor)	EPO; JPO; DERWENT; IBM_TDB	2003/10/28 11:59
7	9	((print with head) and (drive with transistor)) and oxide	EPO; JPO; DERWENT; IBM_TDB	2003/10/28 11:59

L Number	Hits	Search Text	DB	Time stamp
1	17	(print with head) and transistor and oxide	EPO; JPO; DERWENT; IBM_TDB	2003/10/28 14:14
2	452	(print with head) and transistor and oxide	USPAT; US-PGPUB	2003/10/28 14:14
3	384	((print with head) and transistor and oxide) and @ad<20020108	USPAT; US-PGPUB	2003/10/28 14:15

L Number	Hits	Search Text	DB	Time stamp
1	60518	CMOS and @ad<20020108	USPAT; US-PGPUB	2003/10/28 10:04
2	48140	((CMOS and @ad<20020108) and (source or drain))	USPAT; US-PGPUB	2003/10/28 10:04
3	7666	((CMOS and @ad<20020108) and (source or drain)) and ((depositing or deposited) with oxide)	USPAT; US-PGPUB	2003/10/28 10:05
4	7311	((((CMOS and @ad<20020108) and (source or drain)) and ((depositing or deposited) with oxide)) and (gate or electrode)	USPAT; US-PGPUB	2003/10/28 10:05
5	5773	(((((CMOS and @ad<20020108) and (source or drain)) and ((depositing or deposited) with oxide)) and (gate or electrode)) and transistors	USPAT; US-PGPUB	2003/10/28 10:06
6	3639	((((((CMOS and @ad<20020108) and (source or drain)) and ((depositing or deposited) with oxide)) and (gate or electrode)) and transistors) and (implant or implanting)	USPAT; US-PGPUB	2003/10/28 10:06
7	3107	((((((((CMOS and @ad<20020108) and (source or drain)) and ((depositing or deposited) with oxide)) and (gate or electrode)) and transistors) and (implant or implanting)) and polysilicon	USPAT; US-PGPUB	2003/10/28 10:07
8	1963	(((((((((CMOS and @ad<20020108) and (source or drain)) and ((depositing or deposited) with oxide)) and (gate or electrode)) and transistors) and (implant or implanting)) and polysilicon) and (substrate with ((p adj type) or boron))	USPAT; US-PGPUB	2003/10/28 10:08
9	996	(((((((((CMOS and @ad<20020108) and (source or drain)) and ((depositing or deposited) with oxide)) and (gate or electrode)) and transistors) and (implant or implanting)) and polysilicon) and (substrate with ((p adj type) or boron))) and (second with transistor)	USPAT; US-PGPUB	2003/10/28 10:08
10	735	((((((((((CMOS and @ad<20020108) and (source or drain)) and ((depositing or deposited) with oxide)) and (gate or electrode)) and transistors) and (implant or implanting)) and polysilicon) and (substrate with ((p adj type) or boron))) and (second with transistor)) and (n with (doped or doping))	USPAT; US-PGPUB	2003/10/28 10:10